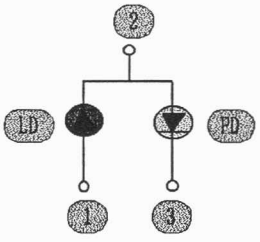
4. SLD63518262 Specifications

■ Description

SLD63518262 is a MOCVD grown 635nm band *InGaAlP* laser diode with quantum well structure. It's an attractive light source, with a typical light output power of 5mW for optoelectronic devices such as laser pointer and Modules.

■ Features

- Visible light output : λ p = 635nm
- Optical power output : 5mW CW
- Built-in photo diode for monitoring laser output
- Package Type : TO-18



■ Absolute maximum ratings (Tc=25℃)

Items	Symbols	Values	Unit
Optical output power	P	7	mW
Laser diode reverse voltage	V	2	V
Photo diode reverse voltage	V	30	V
Operating temperature	Topr	-10 ~ +60	℃
Storage temperature	Tstg	-40 ~ +85	℃

■ Optical and electrical characteristics (Tc=25℃)

Items	Symbols	Min.	Typ.	Max.	Unit	Test Condition
Optical output power	Po	-	5	-	mW	-
Threshold current	Ith	-	30	40	mA	-
Operating current	Iop	-	40	50	mA	Po=5mW
Operating voltage	Vop	-	2.2	2.7	V	Po=5mW
Lasing wavelength	λ p	630	637	645	nm	Po=5mW
Beam divergence	θ ∥	6	8	15	deg	Po=5mW
	θ ⊥	22	35	40	deg	Po=5mW
Beam angle	Δ θ ∥	-	-	± 1.5	deg	Po=5mW
	Δ θ ⊥	-	-	± 2.5	deg	Po=5mW
Monitor current	Im	0.1	0.3	0.5	mA	Po=5mW
Optical distance	Δ X,Δ Y,Δ Z	-	-	± 60	㎛	

NOTICE : Samsung only guarantee SLD63518262 to be operated on APC circuit

Ⅱ. PACKAGE DIMENSIONS